

Applications

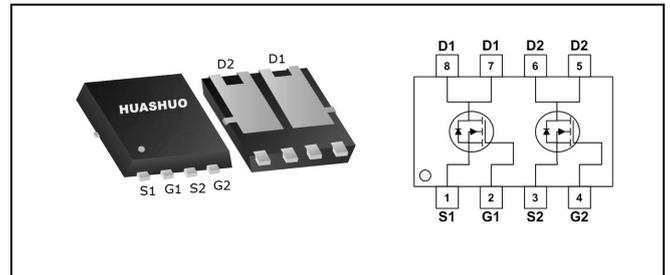
- Power Management in Desktop Computer or DC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial.

Description

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	30	V
$R_{DS(ON),typ}$	5.1	m Ω
I_D	30	A

PRPAK3*3 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_D@T_C=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	23	A
I_{DM}	Pulsed Drain Current ²	100	A
EAS	Single Pulse Avalanche Energy ³	61.3	mJ
I_{AS}	Avalanche Current	35	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	25	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	65	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	8	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA	---	0.021	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =15A	---	5.1	6.3	mΩ
		V _{GS} =4.5V , I _D =10A	---	7.7	9	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.7	2.2	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.73	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =24V , V _{GS} =0V , T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 20V , V _{DS} =0V	---	---	± 100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V , I _D =20A	---	65	---	S
R _g	Gate Resistance	V _{DS} =10V , V _{GS} =0V , f=1MHz	0.8	1.7	2.6	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V , V _{GS} =4.5V , I _D =15A	---	9	---	nC
Q _{gs}	Gate-Source Charge		---	2.8	---	
Q _{gd}	Gate-Drain Charge		---	3.6	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V , V _{GS} =10V , R _G =3Ω I _D =15A	---	7	---	ns
T _r	Rise Time		---	18	---	
T _{d(off)}	Turn-Off Delay Time		---	19	---	
T _f	Fall Time		---	3.4	---	
C _{iss}	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz	---	1113	---	pF
C _{oss}	Output Capacitance		---	436	---	
C _{rss}	Reverse Transfer Capacitance		---	55	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	20	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C	---	---	1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=35A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

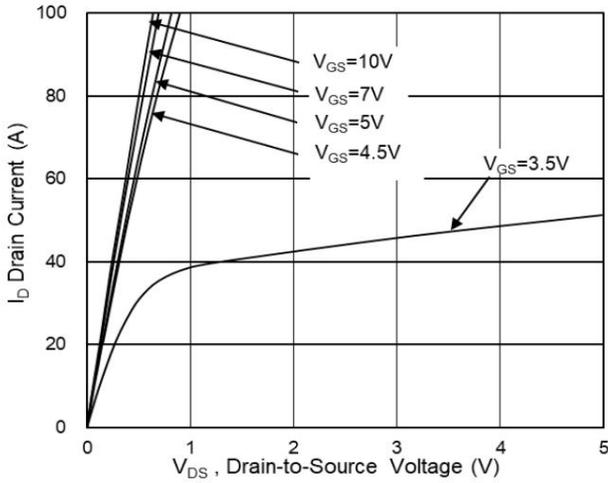


Fig.1 Typical Output Characteristics

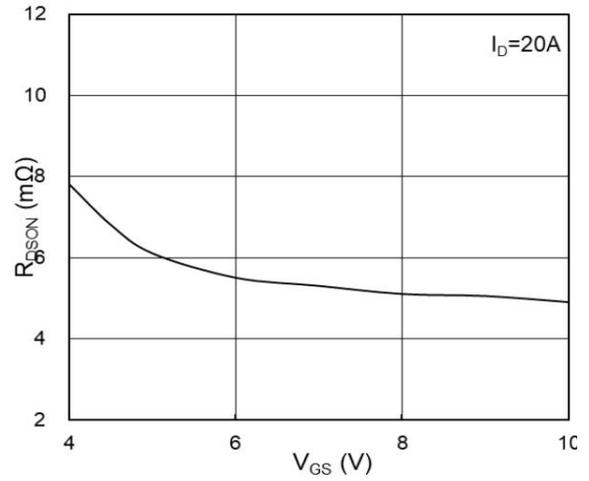


Fig.2 On-Resistance vs. G-S Voltage

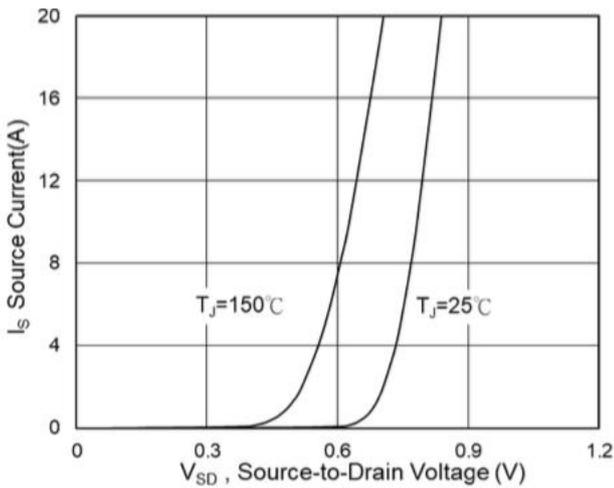


Fig.3 Source Drain Forward Characteristics

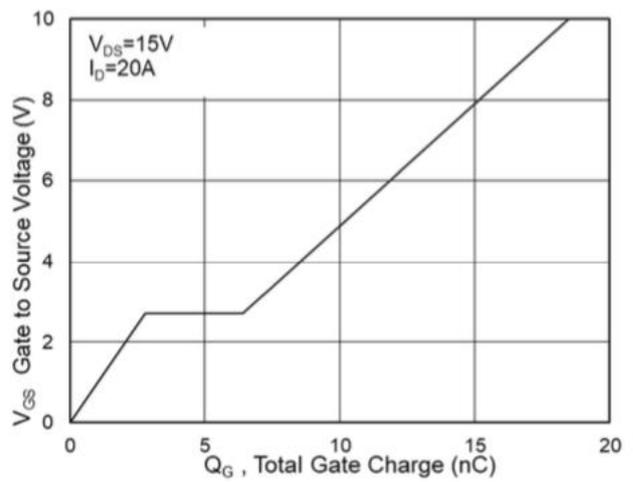


Fig.4 Gate-charge Characteristics

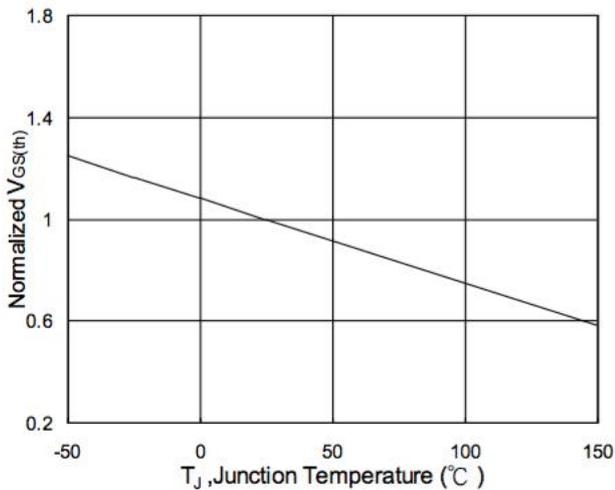


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

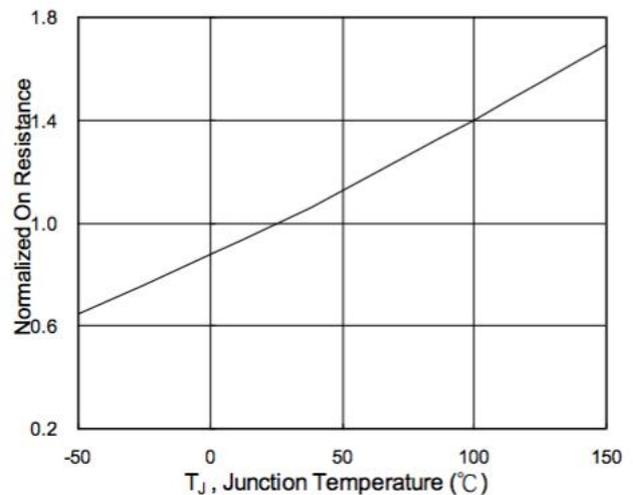


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

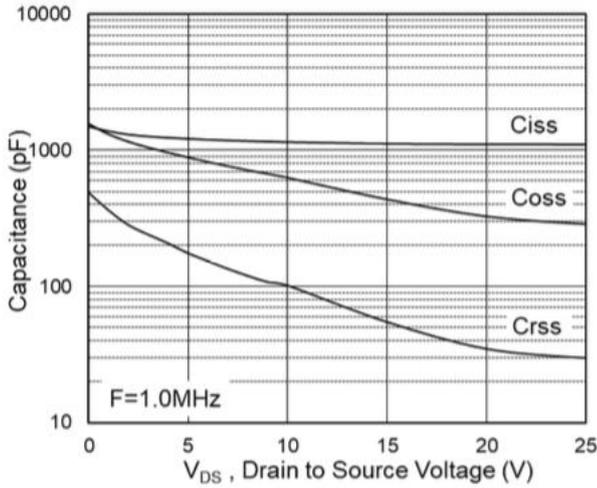


Fig.7 Capacitance

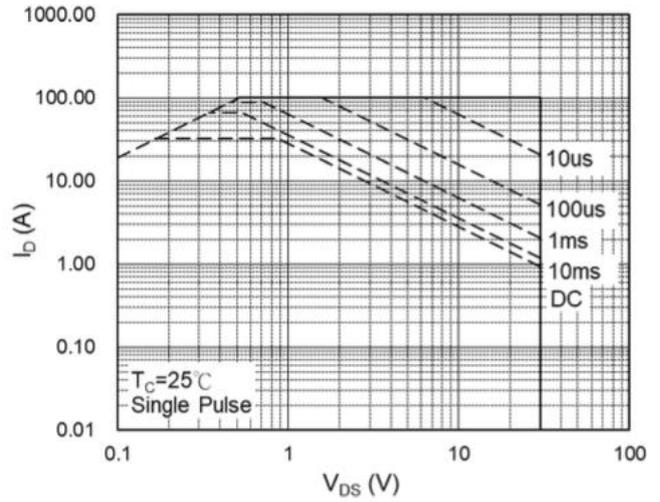


Fig.8 Safe Operating Area

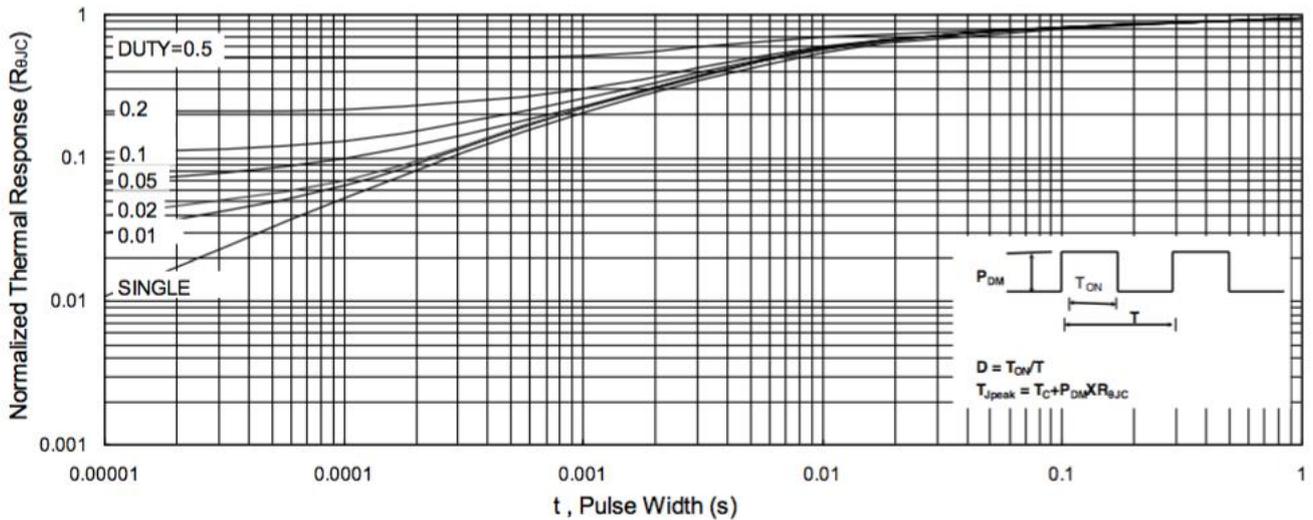


Fig.9 Normalized Maximum Transient Thermal Impedance

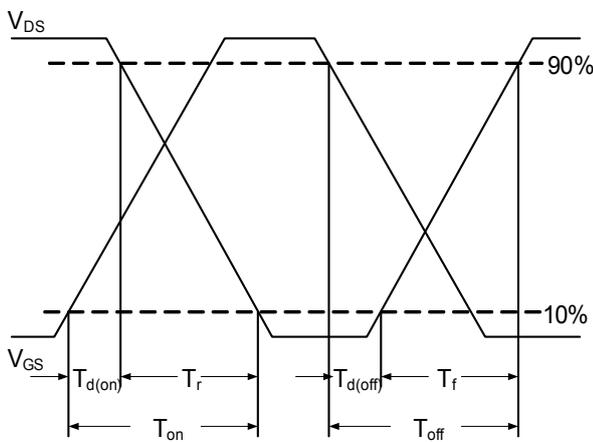


Fig.10 Switching Time Waveform

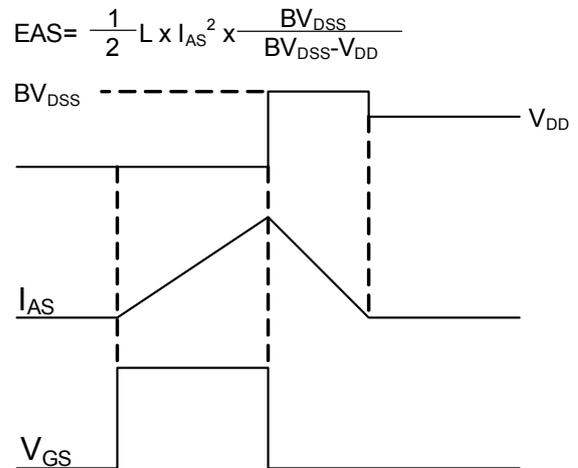
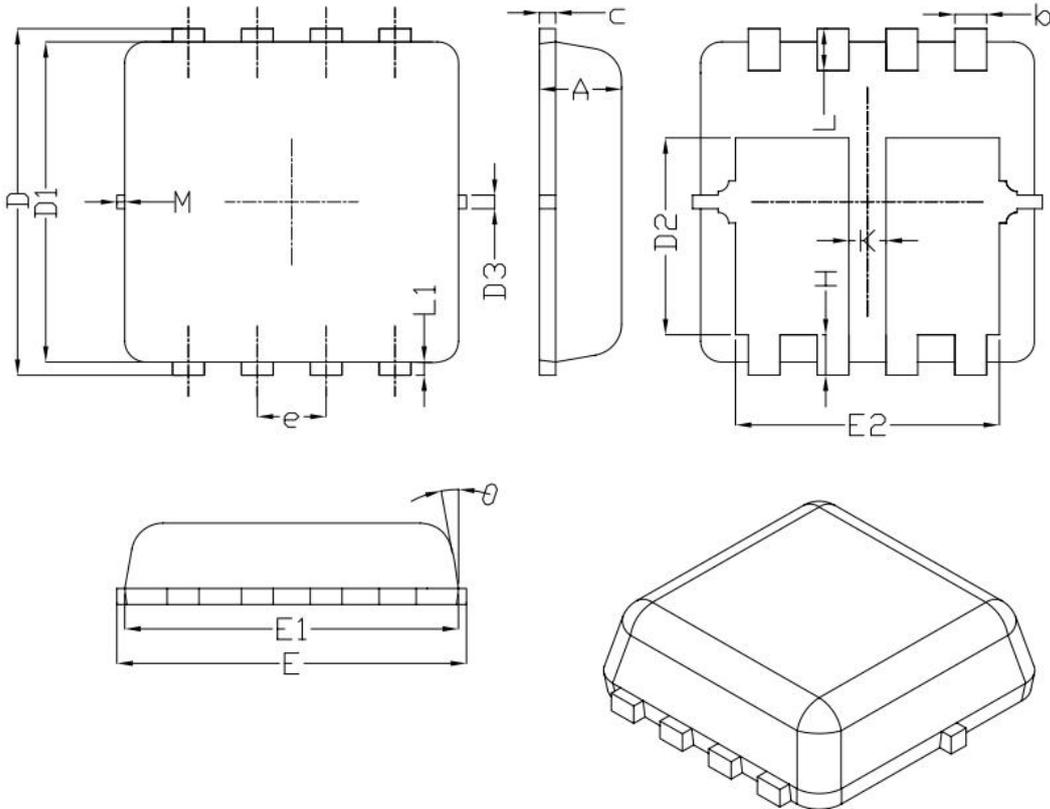


Fig.11 Unclamped Inductive Switching

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



PRPAK3X3 Package Outline Dimensions



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
K	0.30	---	---
theta	---	10°	12°
M	*	*	0.15
* Not specified			